

LE 1965473 A1

L6 ANSWER 24 OF 98 CAPLUS COPYRIGHT 1999 ACS
 AN 1997:502314 CAPLUS

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TI Semiconductor device and its manufacture
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 PA Kabushiki Kaisha Toshiba, Japan
 SO Ger. Offen., 33 pp.

CODEN: GWXXBX

DT Patent

LA German

IC ICM H01L021-31

ICS H01L021-469

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

Section cross-reference(s): 42, 76

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	DE 19654737	A1	19970703	DE 1996-19654737	19961230
	JP 09237785	A2	19970909	JP 1996-68830	19960325
PRAI	JP 1995-342894		19951228		
	JP 1996-68830		19960325		

AB The title device comprises a substrate and at least one interlayer-isolation film or one passivation-isolation film, wherein the film is formed on the substrate and contains Si, O, C and H, where the content of C is not smaller than the content of Si. The isolation film may have a dielec. const. of 1.3-3.2. The isolation film may comprise -(SiR₁R₂-O-SiR₁R₂-O)_n- [R₁ = C_nH_{2n+1}, R₂ = C_nH_{2n+1}, OC_{2n+1}; n, m = d.p.]. The manuf. is carried out by a plasma CVD method.

ST semiconductor device isolation film plasma CVD
 IT Polysiloxanes, processes

RL: DEV (Device component use); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)

IT (isolation film of semiconductor device)
Semiconductor devices

IT (semiconductor device and its manuf.)

75-76-3, Tetramethylsilane 78-10-4, Tetraethoxysilane 631-36-7,
 Tetraethylsilane 681-84-5, Tetramethoxysilane 1450-14-2,
 Hexamethyldisilane 1992-48-9, Tetraisopropoxysilane

RL: PEP (Physical, engineering or chemical process); TEM (Technical or engineered material use); PROC (Process); USES (Uses)

IT (isolation film of semiconductor device prep'd. from)
 124-38-9, Carbon dioxide, reactions 630-08-0, Carbon monoxide, reactions 7722-84-1, Hydrogen peroxide, reactions 7732-18-5, Water, reactions 7782-44-7, Oxygen, reactions 10024-97-2, Nitrogen oxide (N₂O), reactions 10028-15-6, Ozone, reactions 10102-43-9, Nitrogen monoxide, reactions 10102-44-0, Nitrogen dioxide, reactions

RL: RCT (Reactant)
 (isolation film of semiconductor device prep'd. from)

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